



MBR1080CT THRU MBR10100CT

Features

- Metal of siliconrectifier, majonty carrier conducton
- Guard ring for transient protection
- Low power loss high efficiency
- High surge capacity, High current capability

Maximum Ratings

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +175°C

Microsemi Catalog Number	Device Marking	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBR1080CT	MBR1080CT	80V	56V	80V
MBR10100CT	MBR10100CT	100V	70V	100V

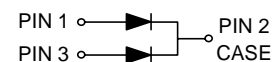
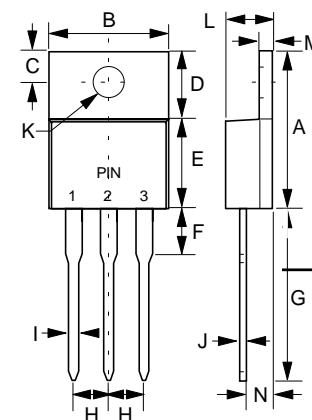
Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	10A	$T_C = 100^\circ\text{C}$
Peak Forward Surge Current	I_{FSM}	120A	8.3ms, half sine
Maximum Forward Voltage Drop Per Element	V_F	.85V .75V	$I_{FM} = 5A$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	0.2mA 15mA	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
Typical Junction Capacitance	C_J	300pF	Measured at 1.0MHz, $V_R=4.0V$

*Pulse test: Pulse width 300 μsec , Duty cycle 2%

10 Amp Schottky Barrier Rectifier 80-100 Volts

TO-220AB



DIM	DIMENSIONS				NOTE
	INCHES		MM		
A	.560	.625	14.22	15.88	
B	.380	.420	9.65	10.67	
C	.100	.135	2.54	3.43	
D	.230	.270	5.84	6.86	
E	.380	.420	9.65	10.67	
F	-----	.250	-----	6.35	
G	.500	.580	12.70	14.73	
H	.090	.110	2.29	2.79	
I	.020	.045	0.51	1.14	
J	.012	.025	0.30	0.64	
K	.139	.161	3.53	4.09	∅
L	.140	.190	3.56	4.83	
M	.045	.055	1.14	1.40	
N	.080	.115	2.03	2.92	

MBR1080CT thru MBR 10100CT
RATING AND CHARACTERISTIC CURVES

FIG.1 - FORWARD CURRENT DERATING CURVE

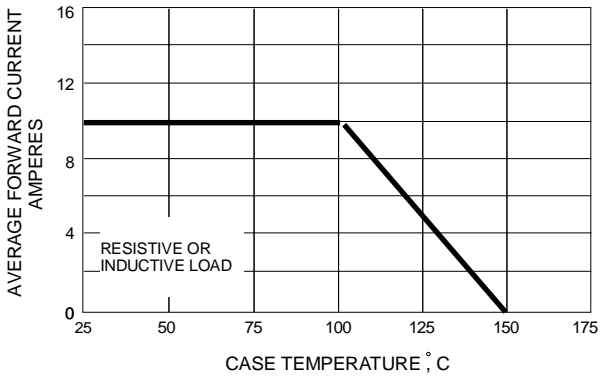


FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

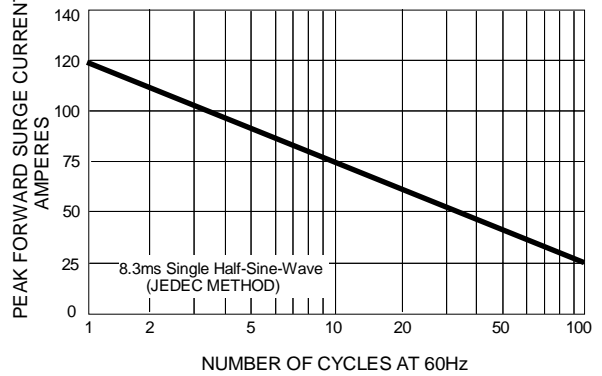


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

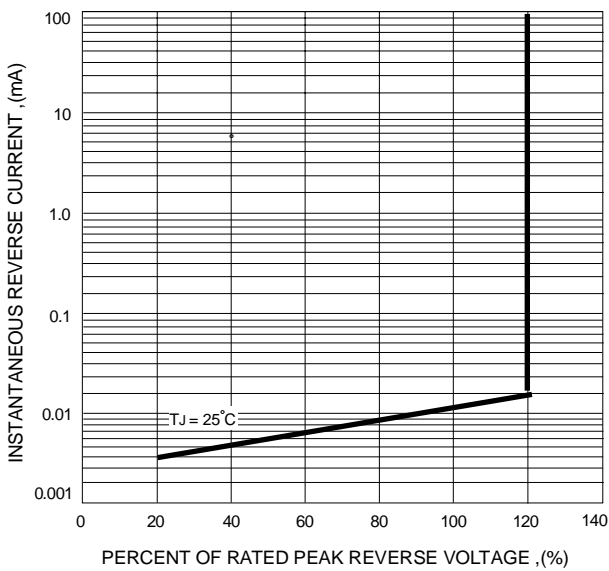


FIG.4 - TYPICAL FORWARD CHARACTERISTICS

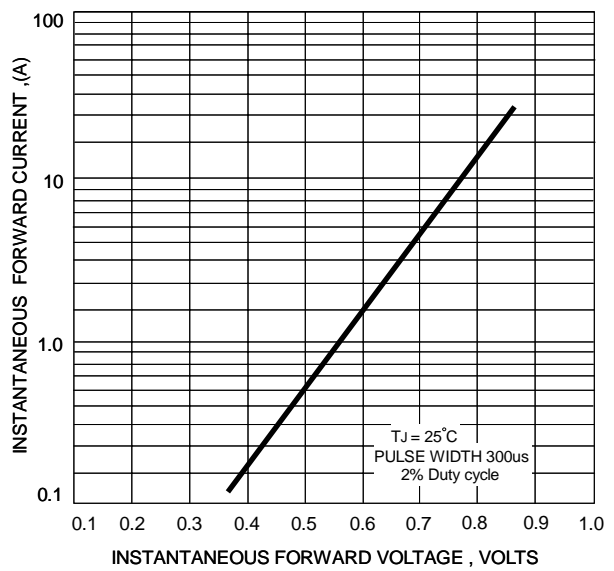


FIG.5 - TYPICAL JUNCTION CAPACITANCE

